

# Gilles Patriarche

## List of Publications by Year in descending order

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650  
papers

15,260  
citations

22153

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38395

95  
g-index

657  
all docs

657  
docs citations

657  
times ranked

13735  
citing authors

#	ARTICLE	IF	CITATIONS
1	Crystal Phase Control during Epitaxial Hybridization of III-V Semiconductors with Silicon. Advanced Electronic Materials, 2022, 8, 2100777.	5.1	18
2	In-situ Transmission Electron Microscopy Observation of Germanium Growth on Freestanding Graphene: Unfolding Mechanism of 3D Crystal Growth During Van der Waals Epitaxy. Small, 2022, 18, e2101890.	10.0	5
3	Up to 300 K lasing with GeSn-On-Insulator microdisk resonators. Optics Express, 2022, 30, 3954.	3.4	16
4	In-plane InGaAs/Ga(As)Sb nanowire based tunnel junctions grown by selective area molecular beam epitaxy. Nanotechnology, 2022, 33, 145201.	2.6	1
5	Influence of Sapphire Substrate Orientation on the van der Waals Epitaxy of III-Nitrides on 2D Hexagonal Boron Nitride: Implication for Optoelectronic Devices. ACS Applied Nano Materials, 2022, 5, 791-800.	5.0	12
6	Nanoindentation investigation of solid-solution strengthening in III-V semiconductor alloys. International Journal of Materials Research, 2022, 96, 1237-1241.	0.3	3
7	Guided-Mode Resonator Coupled with Nanocrystal Intraband Absorption. ACS Photonics, 2022, 9, 985-993.	6.6	10
8	Electroluminescence from nanocrystals above 2 $\mu\text{m}$ . Nature Photonics, 2022, 16, 38-44.	31.4	25
9	Evidence for highly p-type doping and type II band alignment in large scale monolayer WSe <sub>2</sub> /Se-terminated GaAs heterojunction grown by molecular beam epitaxy. Nanoscale, 2022, 14, 5859-5868.	5.6	12
10	Regulated Dynamics with Two Monolayer Steps in Vapor-Solid Growth of Nanowires. ACS Nano, 2022, 16, 4397-4407.	14.6	5
11	Photo-Activated Phosphorescence of Ultrafine ZnS:Mn Quantum Dots: On the Lattice Strain Contribution. Journal of Physical Chemistry C, 2022, 126, 1531-1541.	3.1	1
12	Continuous-Wave Second-Harmonic Generation in Orientation-Patterned Gallium Phosphide Waveguides at Telecom Wavelengths. ACS Photonics, 2022, 9, 2032-2039.	6.6	7
13	Indentation behaviour of (011) thin films of III-V semiconductors: polarity effect differences between GaAs and InP. International Journal of Materials Research, 2022, 97, 1230-1234.	0.3	0
14	Experimental quantification of atomically-resolved HAADF-STEM images using EDX. Ultramicroscopy, 2021, 220, 113152.	1.9	3
15	Engineering a Robust Flat Band in III-V Semiconductor Heterostructures. Nano Letters, 2021, 21, 680-685.	9.1	19
16	Efficient Electrical Transport Through Oxide-Mediated InP-on-Si Hybrid Interfaces Bonded at 300 $^{\circ}\text{C}$ . Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2000317.	1.8	1
17	Topological surface states in epitaxial $\text{Bi}_2\text{Te}_3/\text{Bi}_2\text{Se}_3$ heterostructures		

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19	Development of a cryogenic indentation tool with in situ optical observation, application to the mechanical characterization of II–VI semiconductors. Semiconductor Science and Technology, 2021, 36, 035015.	2.0	2
20	Interdiffusion of Al and Ga in AlN/AlGaN superlattices grown by ammonia-assisted molecular beam epitaxy. Superlattices and Microstructures, 2021, 150, 106801.	3.1	8
21	Strain, magnetic anisotropy, and composition modulation in hybrid metal–oxide vertically assembled nanocomposites. MRS Bulletin, 2021, 46, 136-141.	3.5	5
22	Development of Micron Sized Photonic Devices Based on Deep GaN Etching. Photonics, 2021, 8, 68.	2.0	4
23	Temperature dependence of optical properties of InAs/InP quantum rod-nanowires grown on Si substrate. Journal of Luminescence, 2021, 231, 117814.	3.1	2
24	Degradation Mechanism of Porous Metal-Organic Frameworks by In Situ Atomic Force Microscopy. Nanomaterials, 2021, 11, 722.	4.1	26
25	Band-Gap Landscape Engineering in Large-Scale 2D Semiconductor van der Waals Heterostructures. ACS Nano, 2021, 15, 7279-7289.	14.6	28
26	Fabrication and characterization of ZnO:Sb/n-ZnO homojunctions. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	2.3	2
27	Correlating Structure and Detection Properties in HgTe Nanocrystal Films. Nano Letters, 2021, 21, 4145-4151.	9.1	23
28	Monolithic Free-Standing Large-Area Vertical III-N Light-Emitting Diode Arrays by One-Step h-BN-Based Thermomechanical Self-Lift-Off and Transfer. ACS Applied Electronic Materials, 2021, 3, 2614-2621.	4.3	8
29	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride–A key enabler of III-nitride flexible optoelectronics. APL Materials, 2021, 9, .	5.1	9
30	Spray-Drying Polymer Encapsulation of CsPbBr <sub>3</sub> Perovskite Nanocrystals with Enhanced Photostability for LED Downconverters. ACS Applied Nano Materials, 2021, 4, 7502-7512.	5.0	11
31	Electronic band gap of van der Waals $\pm$ -As <sub>2</sub> Te <sub>3</sub> crystals. Applied Physics Letters, 2021, 119, .	3.3	4
32	Selective target protein detection using a decorated nanopore into a microfluidic device. Biosensors and Bioelectronics, 2021, 183, 113195.	10.1	17
33	Dynamics of Droplet Consumption in Vapor–Liquid–Solid III–V Nanowire Growth. Crystal Growth and Design, 2021, 21, 4647-4655.	3.0	6
34	Single-Electron Tunneling PbS/InP Heterostructure Nanoplatelets for Synaptic Operations. ACS Applied Materials & Interfaces, 2021, 13, 38450-38457.	8.0	3
35	Monodispersed MOF-808 Nanocrystals Synthesized via a Scalable Room-Temperature Approach for Efficient Heterogeneous Peptide Bond Hydrolysis. Chemistry of Materials, 2021, 33, 7057-7066.	6.7	51
36	Relaxation mechanism of GaP grown on 001 Si substrates: influence of defects on the growth of AlGaP layers on GaP/Si templates. Philosophical Magazine, 2021, 101, 2189-2199.	1.6	1

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37	Quantum well interband semiconductor lasers highly tolerant to dislocations. <i>Optica</i> , 2021, 8, 1397.	9.3	14
38	Highly linear polarized emission at telecom bands in InAs/InP quantum dot-nanowires by geometry tailoring. <i>Nanoscale</i> , 2021, 13, 16952-16958.	5.6	1
39	Porous nanoparticles with engineered shells release their drug cargo in cancer cells. <i>International Journal of Pharmaceutics</i> , 2021, 610, 121230.	5.2	7
40	Comparative Study on the Quality of Microcrystalline and Epitaxial Silicon Films Produced by PECVD Using Identical SiF <sub>4</sub> Based Process Conditions. <i>Materials</i> , 2021, 14, 6947.	2.9	2
41	GeSnOI mid-infrared laser technology. <i>Light: Science and Applications</i> , 2021, 10, 232.	16.6	18
42	Effects of nitrogen incorporation and thermal annealing on the optical and spin properties of GaPN dilute nitride alloys. <i>Journal of Alloys and Compounds</i> , 2020, 814, 152233.	5.5	3
43	Molecular-beam epitaxy of GaSb on 6°-offcut (001) Si using a GaAs nucleation layer. <i>Journal of Crystal Growth</i> , 2020, 529, 125299.	1.5	6
44	Gate length dependent transport properties of in-plane core-shell nanowires with raised contacts. <i>Nano Research</i> , 2020, 13, 61-66.	10.4	1
45	Nanoscale electrical analyses of axial-junction GaAsP nanowires for solar cell applications. <i>Nanotechnology</i> , 2020, 31, 145708.	2.6	14
46	Microstructure of GaAs thin films grown on glass using Ge seed layers fabricated by aluminium induced crystallization. <i>Thin Solid Films</i> , 2020, 694, 137737.	1.8	3
47	Control of the Mechanical Adhesion of III-V Materials Grown on Layered h-BN. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 55460-55466.	8.0	14
48	Reduced Lasing Thresholds in GeSn Microdisk Cavities with Defect Management of the Optically Active Region. <i>ACS Photonics</i> , 2020, 7, 2713-2722.	6.6	42
49	Highly Ordered Boron Nitride/Epigraphene Epitaxial Films on Silicon Carbide by Lateral Epitaxial Deposition. <i>ACS Nano</i> , 2020, 14, 12962-12971.	14.6	14
50	Stable and high yield growth of GaP and In <sub>0.2</sub> Ga <sub>0.8</sub> As nanowire arrays using In as a catalyst. <i>Nanoscale</i> , 2020, 12, 18240-18248.	5.6	6
51	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. <i>Scientific Reports</i> , 2020, 10, 21709.	3.3	12
52	Effect of sintering germanium epilayers on dislocation dynamics: From theory to experimental observation. <i>Acta Materialia</i> , 2020, 200, 608-618.	7.9	2
53	Why is it difficult to grow spontaneous ZnO nanowires using molecular beam epitaxy?. <i>Nanotechnology</i> , 2020, 31, 385601.	2.6	4
54	Crystal phase engineering of self-catalyzed GaAs nanowires using a RHEED diagram. <i>Nanoscale Advances</i> , 2020, 2, 2127-2134.	4.6	11

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55	Measuring the surface bonding energy: A comparison between the classical double-cantilever beam experiment and its nanoscale analog. AIP Advances, 2020, 10, 045006.	1.3	1
56	Ultra-low-threshold continuous-wave and pulsed lasing in tensile-strained GeSn alloys. Nature Photonics, 2020, 14, 375-382.	31.4	145
57	Encapsulation of Microperoxidase-8 in MIL-101(Cr)-X Nanoparticles: Influence of Metal-Organic Framework Functionalization on Enzymatic Immobilization and Catalytic Activity. ACS Applied Nano Materials, 2020, 3, 3233-3243.	5.0	26
58	Phase Selection in Self-catalyzed GaAs Nanowires. Nano Letters, 2020, 20, 1669-1675.	9.1	83
59	Pushing Absorption of Perovskite Nanocrystals into the Infrared. Nano Letters, 2020, 20, 3999-4006.	9.1	18
60	Efficient incorporation and protection of lansoprazole in cyclodextrin metal-organic frameworks. International Journal of Pharmaceutics, 2020, 585, 119442.	5.2	15
61	Single crystalline boron rich B(Al)N alloys grown by MOVPE. Applied Physics Letters, 2020, 116, .	3.3	12
62	Engineering dislocations and nanovoids for high-efficiency III-V photovoltaic cells on silicon. AIP Conference Proceedings, 2020, , .	0.4	2
63	Density-controlled growth of vertical InP nanowires on Si(111) substrates. Nanotechnology, 2020, 31, 354003.	2.6	4
64	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. Physical Review Materials, 2020, 4, .	2.4	23
65	Structural, vibrational, and magnetic properties of self-assembled CoPt nanoalloys embedded in SrTiO <sub>3</sub> . Physical Review Materials, 2020, 4, .	2.4	2
66	(Invited) Tensile Strain Engineering and Defects Management in GeSn Laser Cavities. ECS Transactions, 2020, 98, 61-68.	0.5	1
67	3.3 Åm interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. Semiconductor Science and Technology, 2020, 35, 125029.	2.0	6
68	Defects management in the gain media of GeSn micro-disk lasers. , 2020, , .		0
69	Capturing the Effects of Free Surfaces on Threading Dislocation Density Reduction. ECS Transactions, 2020, 98, 527-532.	0.5	1
70	Composition and Face Polarity Influences on Mechanical Properties of (111) Cd <sub>1-x</sub> Zn <sub>y</sub> Te Determined by Indentation. Journal of Electronic Materials, 2019, 48, 6985-6990.	2.2	1
71	Evidence for a narrow band gap phase in 1T <sup>-2</sup> WS <sub>2</sub> nanosheet. Applied Physics Letters, 2019, 115, .	3.3	25
72	Voided Ge/Si Platform to Integrate III-V Materials on Si. ECS Transactions, 2019, 93, 81-85.	0.5	3

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73	Ultra-Low Threshold CW Lasing in Tensile Strained GeSn Microdisk Cavities. , 2019, , .		0
74	Uprooting defects to enable high-performance IIIâ€V optoelectronic devices on silicon. Nature Communications, 2019, 10, 4322.	12.8	44
75	Physical mechanisms involved in the formation and operation of memory devices based on a monolayer of gold nanoparticle-polythiophene hybrid materials. Nanoscale Advances, 2019, 1, 2718-2726.	4.6	8
76	Largeâ€Area van der Waals Epitaxial Growth of Vertical IIIâ€Nitride Nanodevice Structures on Layered Boron Nitride. Advanced Materials Interfaces, 2019, 6, 1900207.	3.7	12
77	GaAs (1 1 1) epilayers grown by MBE on Ge (1 1 1): Twin reduction and polarity. Journal of Crystal Growth, 2019, 519, 84-90.	1.5	13
78	Importance of point defect reactions for the atomic-scale roughness of IIIâ€V nanowire sidewalls. Nanotechnology, 2019, 30, 324002.	2.6	5
79	Evidence and control of unintentional As-rich shells in GaAs<sub>1-x</sub>P<sub>x</sub> nanowires. Nanotechnology, 2019, 30, 294003.	2.6	4
80	Controlled Dislocations Injection in N/P Hg1âˆ’xCdxTe Photodiodes by Indentations. Journal of Electronic Materials, 2019, 48, 6108-6112.	2.2	2
81	Correlated optical and structural analyses of individual GaAsP/GaP coreâ€shell nanowires. Nanotechnology, 2019, 30, 304001.	2.6	7
82	Trap-Free Heterostructure of PbS Nanoplatelets on InP(001) by Chemical Epitaxy. ACS Nano, 2019, 13, 1961-1967.	14.6	7
83	Selective area molecular beam epitaxy of InSb nanostructures on mismatched substrates. Journal of Crystal Growth, 2019, 512, 6-10.	1.5	13
84	InAs quantum dot in a needlelike tapered InP nanowire: a telecom band single photon source monolithically grown on silicon. Nanoscale, 2019, 11, 21847-21855.	5.6	19
85	Wafer-scale MOVPE growth and characterization of highly ordered h-BN on patterned sapphire substrates. Journal of Crystal Growth, 2019, 509, 40-43.	1.5	11
86	InAs/GaSb thin layers directly grown on nominal (0â€0â€1)-Si substrate by MOVPE for the fabrication of InAs FINFET. Journal of Crystal Growth, 2019, 510, 18-22.	1.5	3
87	Development of reflective back contacts for high-efficiency ultrathin Cu(In,Ga)Se2 solar cells. Thin Solid Films, 2019, 672, 1-6.	1.8	22
88	MOVPE van der Waals epitaxial growth of AlGaIn/AlGaIn multiple quantum well structures with deep UV emission on large scale 2D h-BN buffered sapphire substrates. Journal of Crystal Growth, 2019, 507, 352-356.	1.5	8
89	Growth optimization and characterization of regular arrays of GaAs/AlGaAs core/shell nanowires for tandem solar cells on silicon. Nanotechnology, 2019, 30, 084005.	2.6	16
90	Phase separation and surface segregation in Coâ€Auâ€SrTiO3 thin films: Self-assembly of bilayered epitaxial nanocolumnar composites. Physical Review Materials, 2019, 3, .	2.4	4

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91	A study of the strain distribution by scanning X-ray diffraction on GaP/Si for III-V monolithic integration on silicon. Journal of Applied Crystallography, 2019, 52, 809-815.	4.5	2
92	A porous Ge/Si interface layer for defect-free III-V multi-junction solar cells on silicon. , 2019, , .		5
93	Heteroepitaxial growth of silicon on GaAs via low-temperature plasma-enhanced chemical vapor deposition. , 2019, , .		2
94	Polarization- and diffraction-controlled second-harmonic generation from semiconductor metasurfaces. Journal of the Optical Society of America B: Optical Physics, 2019, 36, E55.	2.1	20
95	High structural and optical quality of III-V-on-Si 1.2 nm-thick oxide-bonded hybrid interface. Microelectronic Engineering, 2018, 192, 25-29.	2.4	1
96	Determination of the spin orbit coupling and crystal field splitting in wurtzite InP by polarization resolved photoluminescence. Applied Physics Letters, 2018, 112, .	3.3	4
97	Measuring and Modeling the Growth Dynamics of Self-Catalyzed GaP Nanowire Arrays. Nano Letters, 2018, 18, 701-708.	9.1	55
98	Shear-driven phase transformation in silicon nanowires. Nanotechnology, 2018, 29, 125601.	2.6	28
99	Biomimetic ion channels formation by emulsion based on chemically modified cyclodextrin nanotubes. Faraday Discussions, 2018, 210, 41-54.	3.2	8
100	Quantum cascade lasers grown on silicon. , 2018, , .		0
101	Interface energy analysis of III-V islands on Si (001) in the Volmer-Weber growth mode. Applied Physics Letters, 2018, 113, .	3.3	14
102	Nanoscale investigation of a radial p-n junction in self-catalyzed GaAs nanowires grown on Si (111). Nanoscale, 2018, 10, 20207-20217.	5.6	10
103	Solid-State Nanopore Easy Chip Integration in a Cheap and Reusable Microfluidic Device for Ion Transport and Polymer Conformation Sensing. ACS Sensors, 2018, 3, 2129-2137.	7.8	21
104	Atomic Step Flow on a Nanofacet. Physical Review Letters, 2018, 121, 166101.	7.8	113
105	A Stress-Free and Textured GaP Template on Silicon for Solar Water Splitting. Advanced Functional Materials, 2018, 28, 1801585.	14.9	22
106	Wave-Function Engineering in HgSe/HgTe Colloidal Heterostructures To Enhance Mid-infrared Photoconductive Properties. Nano Letters, 2018, 18, 4590-4597.	9.1	24
107	Coupled HgSe Colloidal Quantum Wells through a Tunable Barrier: A Strategy To Uncouple Optical and Transport Band Gap. Chemistry of Materials, 2018, 30, 4065-4072.	6.7	32
108	In-plane InSb nanowires grown by selective area molecular beam epitaxy on semi-insulating substrate. Nanotechnology, 2018, 29, 305705.	2.6	20

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109	Versatile cyclodextrin nanotube synthesis with functional anchors for efficient ion channel formation: design, characterization and ion conductance. <i>Nanoscale</i> , 2018, 10, 15303-15316.	5.6	11
110	Impact of the sequence of precursor introduction on the growth and properties of atomic layer deposited Al-doped ZnO films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	2.1	11
111	Quantum cascade lasers grown on silicon. <i>Scientific Reports</i> , 2018, 8, 7206.	3.3	56
112	Universal description of III-V/Si epitaxial growth processes. <i>Physical Review Materials</i> , 2018, 2, .	2.4	43
113	Chemical nature of the anion antisite in dilute phosphide $\text{GaAs}_{1-x}\text{P}_x$ alloy. <i>Physical Review Materials</i> , 2018, 2, .	2.4	14
114	Ultrathin Ni nanowires embedded in $\text{SrTiO}_3$ : Vertical epitaxy, strain relaxation mechanisms, and solid-state amorphization. <i>Physical Review Materials</i> , 2018, 2, .	2.4	14
115	Atomic scale analyses of {b Z}-module defects in an NiZr alloy. <i>Acta Crystallographica Section A: Foundations and Advances</i> , 2018, 74, 647-658.	0.1	2
116	Large angle twist-bonded compliant substrates for the epitaxy of lattice mismatched III-V semiconductors. , 2018, , 193-196.		0
117	Z-modules in crystallography: structures and defects. <i>Acta Crystallographica Section A: Foundations and Advances</i> , 2018, 74, e103-e104.	0.1	0
118	Threading dislocation free GaSb nanotemplates grown by selective molecular beam epitaxy on GaAs (001) for in-plane InAs nanowire integration. <i>Journal of Crystal Growth</i> , 2017, 477, 45-49.	1.5	13
119	Nanoselective area growth of defect-free thick indium-rich InGaN nanostructures on sacrificial ZnO templates. <i>Nanotechnology</i> , 2017, 28, 195304.	2.6	1
120	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. <i>Journal of Crystal Growth</i> , 2017, 477, 65-71.	1.5	15
121	Flexible metal-semiconductor-metal device prototype on wafer-scale thick boron nitride layers grown by MOVPE. <i>Scientific Reports</i> , 2017, 7, 786.	3.3	41
122	Morphology and valence band offset of GaSb quantum dots grown on GaP(001) and their evolution upon capping. <i>Nanotechnology</i> , 2017, 28, 225601.	2.6	8
123	Dynamic Characterization of III-Nitride-Based High-Speed Photodiodes. <i>IEEE Photonics Journal</i> , 2017, 9, 1-7.	2.0	20
124	In Situ Optical Monitoring of New Pathways in the Metal-Induced Crystallization of Amorphous Ge. <i>Crystal Growth and Design</i> , 2017, 17, 5783-5789.	3.0	7
125	<i>In situ</i> passivation of GaAsP nanowires. <i>Nanotechnology</i> , 2017, 28, 495707.	2.6	27
126	Electronic properties of (Sb;Bi) <sub>2</sub> Te <sub>3</sub> colloidal heterostructured nanoplates down to the single particle level. <i>Scientific Reports</i> , 2017, 7, 9647.	3.3	7



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127	Emission wavelength red-shift by using "semi-bulk" InGaN buffer layer in InGaN/InGaN multiple-quantum-well. Superlattices and Microstructures, 2017, 112, 279-286.	3.1	7
128	Surface effects on exciton diffusion in non polar ZnO/ZnMgO heterostructures. Journal of Physics Condensed Matter, 2017, 29, 485706.	1.8	2
129	Functionalized Solid-State Nanopore Integrated in a Reusable Microfluidic Device for a Better Stability and Nanoparticle Detection. ACS Applied Materials & Interfaces, 2017, 9, 41634-41640.	8.0	42
130	Gas sensors boosted by two-dimensional h-BN enabled transfer on thin substrate foils: towards wearable and portable applications. Scientific Reports, 2017, 7, 15212.	3.3	54
131	Enhanced sputtering of Ge nanowires under synergetic effect of Mn ion and electron beams. Results in Physics, 2017, 7, 3813-3814.	4.1	0
132	Study of the nucleation and growth of InP nanowires on silicon with gold-indium catalyst. Journal of Crystal Growth, 2017, 458, 96-102.	1.5	7
133	Improving InGaN heterojunction solar cells efficiency using a semibulk absorber. Solar Energy Materials and Solar Cells, 2017, 159, 405-411.	6.2	23
134	Mask effect in nano-selective- area-growth by MOCVD on thickness enhancement, indium incorporation, and emission of InGaN nanostructures on AlN-buffered Si(111) substrates. Optical Materials Express, 2017, 7, 376.	3.0	4
135	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. Optical Materials Express, 2017, 7, 3011.	3.0	14
136	III-V Nanowires on Silicon: a possible route to Si-based tandem solar cells. , 2017, , .		0
137	Ultrathin PECVD epitaxial Si solar cells on glass via low-temperature transfer process. Progress in Photovoltaics: Research and Applications, 2016, 24, 1075-1084.	8.1	32
138	Wetâ€Route Synthesis and Characterization of Yb:CaF <sub>2</sub> Optical Ceramics. Journal of the American Ceramic Society, 2016, 99, 1992-2000.	3.8	39
139	Synthesis of In <sub>0.1</sub> Ga <sub>0.9</sub> N/GaN structures grown by MOCVD and MBE for high speed optoelectronics. MRS Advances, 2016, 1, 1735-1742.	0.9	7
140	Selective area heteroepitaxy of GaSb on GaAs (001) for in-plane InAs nanowire achievement. Nanotechnology, 2016, 27, 505301.	2.6	31
141	Nanoparticle Electrical Analysis and Detection with a Solid-state Nanopore in a Microfluidic Device. Procedia Engineering, 2016, 168, 1475-1478.	1.2	3
142	Probing the electronic properties of CVD graphene superlattices. , 2016, , .		1
143	Nanoselective area growth of GaN by metalorganic vapor phase epitaxy on 4H-SiC using epitaxial graphene as a mask. Applied Physics Letters, 2016, 108, .	3.3	15
144	New insights into the Mo/Cu(In,Ga)Se <sub>2</sub> interface in thin film solar cells: Formation and properties of the MoSe <sub>2</sub> interfacial layer. Journal of Chemical Physics, 2016, 145, 154702.	3.0	28

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145	Role of V-pits in the performance improvement of InGaN solar cells. Applied Physics Letters, 2016, 109, .	3.3	8
146	Low temperature plasma enhanced CVD epitaxial growth of silicon on GaAs: a new paradigm for III-V/Si integration. Scientific Reports, 2016, 6, 25674.	3.3	28
147	High reflectance dielectric distributed Bragg reflectors for near ultra-violet planar microcavities: SiO <sub>2</sub> /HfO <sub>2</sub> versus SiO <sub>2</sub> /SiN <sub>x</sub> . Journal of Applied Physics, 2016, 120, .	2.5	6
148	Local probing of the interfacial strength in InP/Si substructures. MRS Advances, 2016, 1, 779-784.	0.9	0
149	Single-crystal nanopyramidal BGaN by nanoselective area growth on AlN/Si(111) and GaN templates. Nanotechnology, 2016, 27, 115602.	2.6	4
150	Pressure-Dependent Photoluminescence Study of Wurtzite InP Nanowires. Nano Letters, 2016, 16, 2926-2930.	9.1	21
151	Large-Area Two-Dimensional Layered Hexagonal Boron Nitride Grown on Sapphire by Metalorganic Vapor Phase Epitaxy. Crystal Growth and Design, 2016, 16, 3409-3415.	3.0	106
152	First orientation-patterned GaSb ridge waveguides fabrication and preliminary characterization for frequency conversion in the mid-infrared. Proceedings of SPIE, 2016, , .	0.8	1
153	(Invited) Locally Measuring the Adhesion of InP Membranes Directly Bonded on Silicon. ECS Transactions, 2016, 75, 169-176.	0.5	0
154	van der Waals Epitaxy of GaSe/Graphene Heterostructure: Electronic and Interfacial Properties. ACS Nano, 2016, 10, 9679-9686.	14.6	154
155	Lazarevicite-type short-range ordering in ternary III-V nanowires. Physical Review B, 2016, 94, .	3.2	7
156	Selective CO <sub>2</sub> methanation on Ru/TiO <sub>2</sub> catalysts: unravelling the decisive role of the TiO <sub>2</sub> support crystal structure. Catalysis Science and Technology, 2016, 6, 8117-8128.	4.1	84
157	Publisher's Note: Interplay between tightly focused excitation and ballistic propagation of polariton condensates in a ZnO microcavity [Phys. Rev. B92, 235308 (2015)]. Physical Review B, 2016, 93, .	3.2	0
158	Mechanistic Insight and Optimization of InP Nanocrystals Synthesized with Aminophosphines. Chemistry of Materials, 2016, 28, 5925-5934.	6.7	93
159	Band Alignment and Minigaps in Monolayer MoS <sub>2</sub> -Graphene van der Waals Heterostructures. Nano Letters, 2016, 16, 4054-4061.	9.1	288
160	Sub-nanometrically resolved chemical mappings of quantum-cascade laser active regions. Semiconductor Science and Technology, 2016, 31, 055017.	2.0	6
161	Metallic Functionalization of CdSe 2D Nanoplatelets and Its Impact on Electronic Transport. Journal of Physical Chemistry C, 2016, 120, 12351-12361.	3.1	29
162	Nondestructive Characterization of Residual Threading Dislocation Density in HgCdTe Layers Grown on CdZnTe by Liquid-Phase Epitaxy. Journal of Electronic Materials, 2016, 45, 4518-4523.	2.2	4

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164	Infrared Photodetection Based on Colloidal Quantum-Dot Films with High Mobility and Optical Absorption up to THz. Nano Letters, 2016, 16, 1282-1286.	9.1	150
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